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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V2
Core Size	32-Bit Single-Core
Speed	66MHz
Connectivity	I²C, SPI, UART/USART, USB OTG
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	55
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	81-LBGA
Supplier Device Package	81-MAPBGA (10x10)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf52210cvm66

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1.1 Block Diagram

Figure 1 shows a top-level block diagram of the device. Package options for this family are described later in this document.

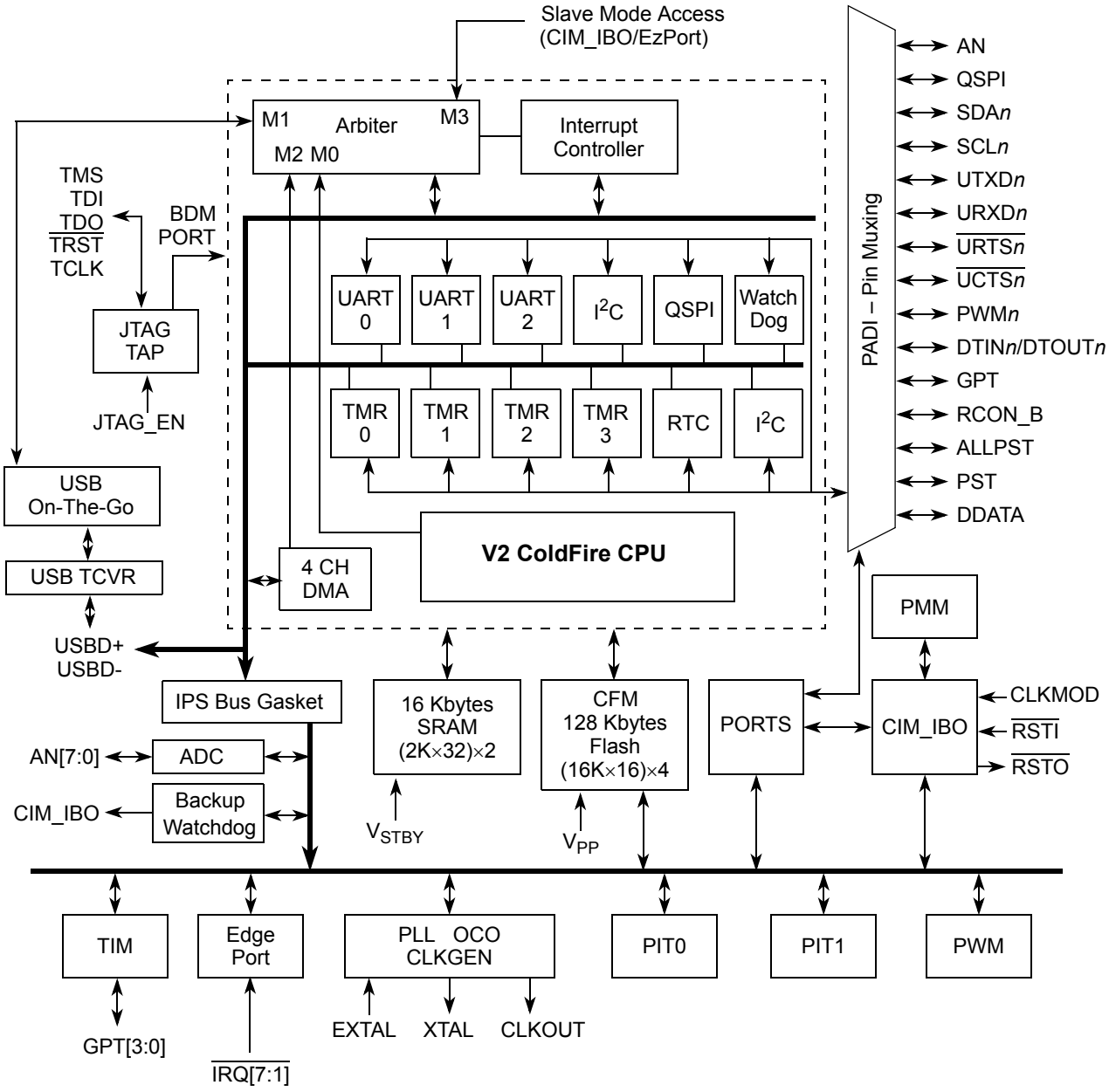


Figure 1. Block Diagram

The full debug/trace interface is available only on the 100-pin packages. However, every product features the dedicated debug serial communication channel (DSI, DSO, DSCLK) and the ALLPST signal.

1.2.4 JTAG

The processor supports circuit board test strategies based on the Test Technology Committee of IEEE and the Joint Test Action Group (JTAG). The test logic includes a test access port (TAP) consisting of a 16-state controller, an instruction register, and three test registers (a 1-bit bypass register, a 256-bit boundary-scan register, and a 32-bit ID register). The boundary scan register links the device's pins into one shift register. Test logic, implemented using static logic design, is independent of the device system logic.

The device implementation can:

- Perform boundary-scan operations to test circuit board electrical continuity
- Sample system pins during operation and transparently shift out the result in the boundary scan register
- Bypass the device for a given circuit board test by effectively reducing the boundary-scan register to a single bit
- Disable the output drive to pins during circuit-board testing
- Drive output pins to stable levels

1.2.5 On-Chip Memories

1.2.5.1 SRAM

The dual-ported SRAM module provides a general-purpose 8- or 16-Kbyte memory block that the ColdFire core can access in a single cycle. The location of the memory block can be set to any 8- or 16-Kbyte boundary within the 4-Gbyte address space. This memory is ideal for storing critical code or data structures and for use as the system stack. Because the SRAM module is physically connected to the processor's high-speed local bus, it can quickly service core-initiated accesses or memory-referencing commands from the debug module.

The SRAM module is also accessible by the DMA. The dual-ported nature of the SRAM makes it ideal for implementing applications with double-buffer schemes, where the processor and a DMA device operate in alternate regions of the SRAM to maximize system performance.

1.2.5.2 Flash Memory

The ColdFire flash module (CFM) is a non-volatile memory (NVM) module that connects to the processor's high-speed local bus. The CFM is constructed with up to four banks of 16-Kbyte×16-bit flash memory arrays to generate up to 128 Kbytes of 32-bit flash memory. These electrically erasable and programmable arrays serve as non-volatile program and data memory. The flash memory is ideal for program and data storage for single-chip applications, allowing for field reprogramming without requiring an external high voltage source. The CFM interfaces to the ColdFire core through an optimized read-only memory controller that supports interleaved accesses from the 2-cycle flash memory arrays. A backdoor mapping of the flash memory is used for all program, erase, and verify operations, as well as providing a read datapath for the DMA. Flash memory may also be programmed via the EzPort, which is a serial flash memory programming interface that allows the flash memory to be read, erased and programmed by an external controller in a format compatible with most SPI bus flash memory chips.

1.2.6 Power Management

The device incorporates several low-power modes of operation entered under program control and exited by several external trigger events. An integrated power-on reset (POR) circuit monitors the input supply and forces an MCU reset as the supply voltage rises. The low voltage detector (LVD) monitors the supply voltage and is configurable to force a reset or interrupt condition if it falls below the LVD trip point. The RAM standby switch provides power to RAM when the supply voltage to the chip falls below the standby battery voltage.

1.2.20 Interrupt Controller (INTC)

The device has a single interrupt controller that supports up to 63 interrupt sources. There are 56 programmable sources, 49 of which are assigned to unique peripheral interrupt requests. The remaining seven sources are unassigned and may be used for software interrupt requests.

1.2.21 DMA Controller

The direct memory access (DMA) controller provides an efficient way to move blocks of data with minimal processor intervention. It has four channels that allow byte, word, longword, or 16-byte burst line transfers. These transfers are triggered by software explicitly setting a DCR*n*[START] bit or by the occurrence of certain UART or DMA timer events.

1.2.22 Reset

The reset controller determines the source of reset, asserts the appropriate reset signals to the system, and keeps track of what caused the last reset. There are seven sources of reset:

- External reset input
- Power-on reset (POR)
- Watchdog timer
- Phase locked-loop (PLL) loss of lock / loss of clock
- Software
- Low-voltage detector (LVD)
- JTAG

Control of the LVD and its associated reset and interrupt are managed by the reset controller. Other registers provide status flags indicating the last source of reset and a control bit for software assertion of the $\overline{\text{RSTO}}$ pin.

1.2.23 GPIO

Nearly all pins on the device have general purpose I/O capability and are grouped into 8-bit ports. Some ports do not use all eight bits. Each port has registers that configure, monitor, and control the port pin.

1.2.24 Part Numbers and Packaging

This product is RoHS-compliant. Refer to the product page at freescale.com or contact your sales office for up-to-date RoHS information.

Table 2. Orderable Part Number Summary

Freescale Part Number	Description	Speed (MHz)	Flash/SRAM (Kbytes)	Package	Temp range (°C)
MCF52210CAE66	MCF52210 Microcontroller, 2 UARTs	66	64 / 16	64 LQFP	-40 to +85
MCF52210CEP66	MCF52210 Microcontroller, 2 UARTs	66	64 / 16	64 QFN	-40 to +85
MCF52210CVM66	MCF52210 Microcontroller, 2 UARTs	66	64 / 16	81 MAPBGA	-40 to +85
MCF52210CVM80	MCF52210 Microcontroller, 2 UARTs	80	64 / 16	81 MAPBGA	-40 to +85
MCF52211CAE66	MCF52211 Microcontroller, 2 UARTs	66	128 / 16	64 LQFP	-40 to +85
MCF52211CAF80	MCF52211 Microcontroller, 3 UARTs	80	128 / 16	100 LQFP	-40 to +85
MCF52211CEP66	MCF52211 Microcontroller, 2 UARTs	66	128 / 16	64 QFN	-40 to +85

Table 2 shows the pinout configuration for the 100 LQFP.

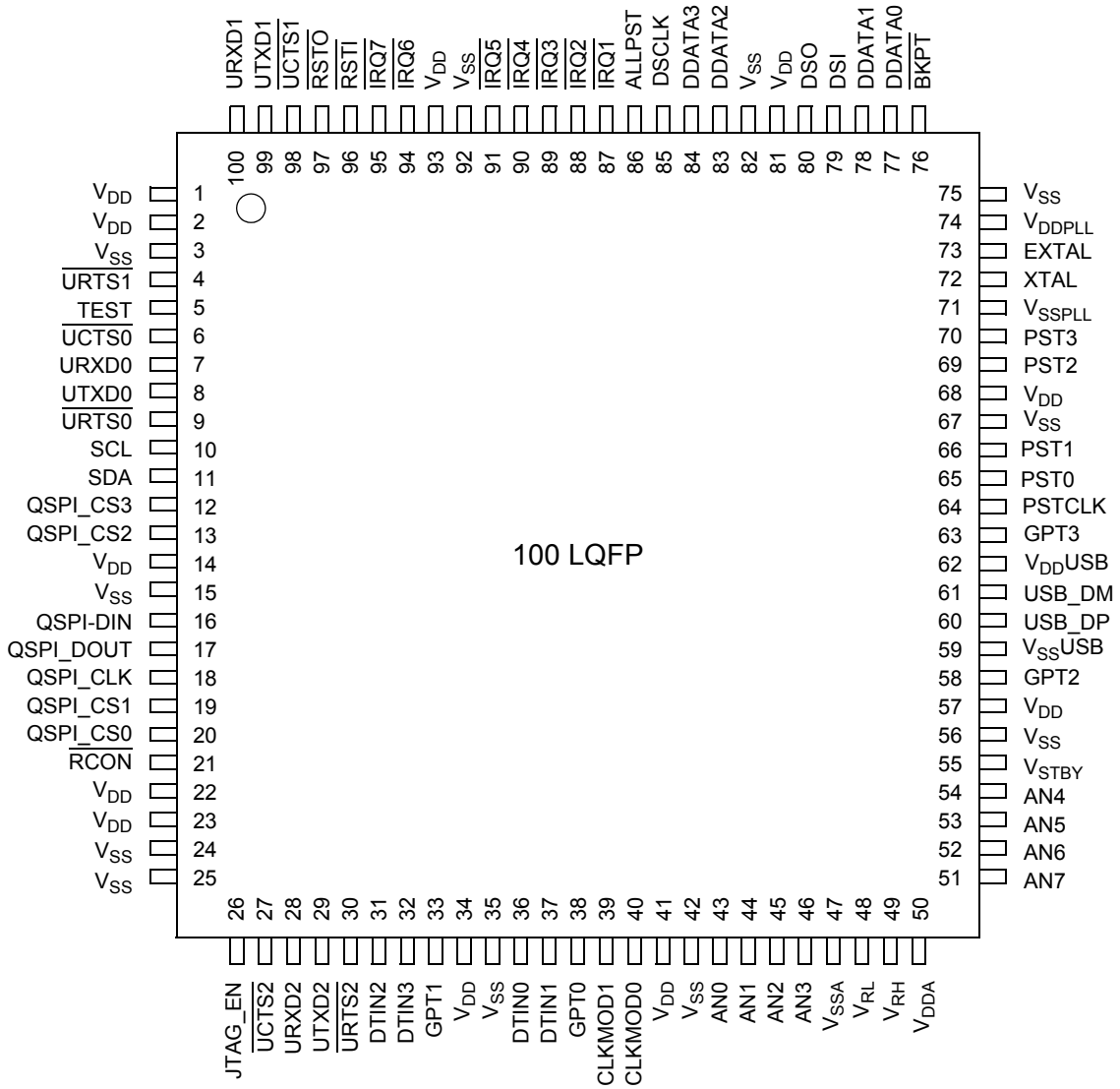


Figure 2. 100 LQFP Pin Assignments

Figure 3 shows the pinout configuration for the 81 MAPBGA.

	1	2	3	4	5	6	7	8	9
A	V_{SS}	UTXD1	$\overline{\text{RSTI}}$	$\overline{\text{IRQ5}}$	$\overline{\text{IRQ3}}$	ALLPST	TDO	TMS	V_{SS}
B	$\overline{\text{URTS1}}$	URXD1	$\overline{\text{RSTO}}$	$\overline{\text{IRQ6}}$	$\overline{\text{IRQ2}}$	$\overline{\text{TRST}}$	TDI	V_{DD}PLL	EXTAL
C	$\overline{\text{UCTS0}}$	TEST	$\overline{\text{UCTS1}}$	$\overline{\text{IRQ7}}$	$\overline{\text{IRQ4}}$	$\overline{\text{IRQ1}}$	TCLK	V_{SS}PLL	XTAL
D	URXD0	UTXD0	$\overline{\text{URTS0}}$	V_{SS}	V_{DD}	V_{SS}	PWM7	GPT3	GPT2
E	SCL	SDA	V_{DD}	V_{DD}	V_{DD}	V_{DD}	V_{DD}	PWM5	GPT1
F	QSPI_CS3	QSPI_CS2	QSPI_DIN	V_{SS}	V_{DD}	V_{SS}	GPT0	V_{STBY}	AN4
G	QSPI_DOUT	QSPI_CLK	$\overline{\text{RCON}}$	DTIN1	CLKMOD0	AN2	AN3	AN5	AN6
H	QSPI_CS0	QSPI_CS1	DTIN3	DTIN0	CLKMOD1	AN1	V_{SSA}	V_{DDA}	AN7
J	V_{SS}	JTAG_EN	DTIN2	PWM3	PWM1	AN0	V_{RL}	V_{RH}	V_{SSA}

Figure 3. 81 MAPBGA Pin Assignments

Table 3 shows the pin functions by primary and alternate purpose, and illustrates which packages contain each pin.

Table 3. Pin Functions by Primary and Alternate Purpose

Pin Group	Primary Function	Secondary Function	Tertiary Function	Quaternary Function	Drive Strength / Control[1]	Slew Rate / Control[1]	Pull-up / Pull-down[2]	Pin on 100 LQFP	Pin on 81 MAPBGA	Pin on 64 LQFP/QFN
ADC	AN7	—	—	GPIO	Low	FAST	—	51	H9	33
	AN6	—	—	GPIO	Low	FAST	—	52	G9	34
	AN5	—	—	GPIO	Low	FAST	—	53	G8	35
	AN4	—	—	GPIO	Low	FAST	—	54	F9	36
	AN3	—	—	GPIO	Low	FAST	—	46	G7	28
	AN2	—	—	GPIO	Low	FAST	—	45	G6	27
	AN1	—	—	GPIO	Low	FAST	—	44	H6	26
	AN0	—	—	GPIO	Low	FAST	—	43	J6	25
	SYNCA[3]	—	—	—	N/A	N/A	—	—	—	—
	SYNCB[3]	—	—	—	N/A	N/A	—	—	—	—
	VDDA	—	—	—	N/A	N/A	—	50	H8	32
	VSSA	—	—	—	N/A	N/A	—	47	H7, J9	29
	VRH	—	—	—	N/A	N/A	—	49	J8	31
	VRL	—	—	—	N/A	N/A	—	48	J7	30
Clock Generation	EXTAL	—	—	—	N/A	N/A	—	73	B9	47
	XTAL	—	—	—	N/A	N/A	—	72	C9	46
	VDDPLL	—	—	—	N/A	N/A	—	74	B8	48
	VSSPLL	—	—	—	N/A	N/A	—	71	C8	45
Debug Data	ALLPST	—	—	—	High	FAST	—	86	A6	55
	DDATA[3:0]	—	—	GPIO	High	FAST	—	84,83,78,77	—	—
	PST[3:0]	—	—	GPIO	High	FAST	—	70,69,66,65	—	—
I^2C	SCL	USB_DMI	UTXD2	GPIO	PDSR[0]	PSRR[0]	pull-up[4]	10	E1	8
	SDA	USB_DPI	URXD2	GPIO	PDSR[0]	PSRR[0]	pull-up[4]	11	E2	9

2 Electrical Characteristics

This section contains electrical specification tables and reference timing diagrams for the microcontroller unit, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

NOTE

The parameters specified in this data sheet supersede any values found in the module specifications.

2.1 Maximum Ratings

Table 19. Absolute Maximum Ratings[1, 2]

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to +4.0	V
Clock synthesizer supply voltage	V_{DDPLL}	–0.3 to +4.0	V
RAM standby supply voltage	V_{STBY}	+1.8 to 3.5	V
USB standby supply voltage	V_{DDUSB}	–0.3 to +4.0	V
Digital input voltage [3]	V_{IN}	–0.3 to +4.0	V
EXTAL pin voltage	V_{EXTAL}	0 to 3.3	V
XTAL pin voltage	V_{XTAL}	0 to 3.3	V
Instantaneous maximum current Single pin limit (applies to all pins)[4, 5]	I_{DD}	25	mA
Operating temperature range (packaged)	T_A (T_L - T_H)	–40 to 85 or 0 to 70[6]	°C
Storage temperature range	T_{stg}	–65 to 150	°C

1 Functional operating conditions are given in DC Electrical Specifications. Absolute Maximum Ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond those listed may affect device reliability or cause permanent damage to the device.

2 This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (V_{SS} or V_{DD}).

3 Input must be current limited to the I_{DD} value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

4 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

5 The power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{in} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in the external power supply going out of regulation. Ensure that the external V_{DD} load shunts current greater than maximum injection current. This is the greatest risk when the MCU is not consuming power (e.g., no clock).

6 Depending on the packaging; see the orderable part number summary.

2.2 Current Consumption

Table 20. Current Consumption in Low-Power Mode[1,2]

Mode	Flash memory				SRAM				Units
	8 MHz	16 MHz	64 MHz	80 MHz	8 MHz	16 MHz	64 MHz	80 MHz	
Stop mode 3 (Stop 11)[3]	0.057				0.002				mA
Stop mode 2 (Stop 10)[3]	2.5				2.3				
Stop mode 1 (Stop 01)[3,4]	3.03	3.3	4.9	5.6	2.9	3.1	4.8	5.4	
Stop mode 0 (Stop 00)[3]	3.03	3.3	4.9	5.6	2.9	3.1	4.8	5.4	
Wait / Doze	12.3	22.7	40.3	45	5.3	7.9	24	30	
Run	TBD	TBD	TBD	TBD	6.7	10.8	35	43	

1 All values are measured with a 3.30V power supply.
2 Refer to the Power Management chapter in the MCF52211 Reference Manual for more information on low-power modes.
3 See the description of the Low-Power Control Register (LPCR) in the MCF52211 Reference Manual for more information on stop modes 0–3.
4 Results are identical to STOP 00 for typical values because they only differ by CLKOUT power consumption. CLKOUT is already disabled in this instance prior to entering low power mode.

Table 21. Typical Active Current Consumption Specifications

Characteristic	Symbol	Typical[1] Active (SRAM)	Typical[1] Active (Flash)	Peak[2] (Flash)	Unit
PLL @ 8 MHz	I_{DD}	8	11	21	mA
PLL @ 16 MHz		12	19	38	
PLL @ 64 MHz		38	45	102	
PLL @ 80 MHz		45	54	118	
RAM standby supply current • Normal operation: $V_{DD} > V_{STBY} - 0.3$ V • Transient condition: $V_{STBY} - 0.3$ V > $V_{DD} > V_{SS} + 0.5$ V • Standby operation: $V_{DD} < V_{SS} + 0.5$ V	I_{STBY}	— —		0 65 16	µA µA µA
Analog supply current • Normal operation • Standby • Powered down	I_{DDA}	— — —	— — —	14 0.8 0	mA
USB supply current	I_{DDUSB}	—	—	TBD	mA
PLL supply current	I_{DDPLL}	—	—	6(see note 3)	mA

1 Tested at room temperature with CPU polling a status register. All clocks were off except the UART and CFM (when running from flash memory).
2 Peak current measured with all modules active, CPU polling a status register, and default drive strength with matching load.
3 Tested with the PLL MFD set to 7 (max value). Setting the MFD to a lower value results in lower current consumption.

2.3 Thermal Characteristics

Table 22 lists thermal resistance values.

Table 22. Thermal Characteristics

	Characteristic		Symbol	Value	Unit
100 LQFP	Junction to ambient, natural convection	Single layer board (1s)	θ_{JA}	53[1,2]	°C/W
	Junction to ambient, natural convection	Four layer board (2s2p)	θ_{JA}	39[1,3]	°C/W
	Junction to ambient, (@200 ft/min)	Single layer board (1s)	θ_{JMA}	42[1,3]	°C/W
	Junction to ambient, (@200 ft/min)	Four layer board (2s2p)	θ_{JMA}	33[1,3]	°C/W
	Junction to board	—	θ_{JB}	25[4]	°C/W
	Junction to case	—	θ_{JC}	9[5]	°C/W
	Junction to top of package	Natural convection	Ψ_{jt}	2[6]	°C/W
	Maximum operating junction temperature	—	T_j	105	°C
81 MAPBGA	Junction to ambient, natural convection	Single layer board (1s)	θ_{JA}	61[1,2]	°C/W
	Junction to ambient, natural convection	Four layer board (2s2p)	θ_{JA}	35[2,3]	°C/W
	Junction to ambient, (@200 ft/min)	Single layer board (1s)	θ_{JMA}	50[2,3]	°C/W
	Junction to ambient, (@200 ft/min)	Four layer board (2s2p)	θ_{JMA}	31[2,3]	°C/W
	Junction to board	—	θ_{JB}	20[4]	°C/W
	Junction to case	—	θ_{JC}	12[5]	°C/W
	Junction to top of package	Natural convection	Ψ_{jt}	2[6]	°C/W
	Maximum operating junction temperature	—	T_j	105	°C
64 LQFP	Junction to ambient, natural convection	Single layer board (1s)	θ_{JA}	62[1,2]	°C/W
	Junction to ambient, natural convection	Four layer board (2s2p)	θ_{JA}	43[1,3]	°C/W
	Junction to ambient (@200 ft/min)	Single layer board (1s)	θ_{JMA}	50[1,3]	°C/W
	Junction to ambient (@200 ft/min)	Four layer board (2s2p)	θ_{JMA}	36[1,3]	°C/W
	Junction to board	—	θ_{JB}	26[4]	°C/W
	Junction to case	—	θ_{JC}	9[5]	°C/W
	Junction to top of package	Natural convection	Ψ_{jt}	2[6]	°C/W
	Maximum operating junction temperature	—	T_j	105	°C
64 QFN	Junction to ambient, natural convection	Single layer board (1s)	θ_{JA}	68[1,2]	°C/W
	Junction to ambient, natural convection	Four layer board (2s2p)	θ_{JA}	24[1,3]	°C/W
	Junction to ambient (@200 ft/min)	Single layer board (1s)	θ_{JMA}	55[1,3]	°C/W
	Junction to ambient (@200 ft/min)	Four layer board (2s2p)	θ_{JMA}	19[1,3]	°C/W
	Junction to board	—	θ_{JB}	8[4]	°C/W
	Junction to case (bottom)	—	θ_{JC}	0.6[5]	°C/W
	Junction to top of package	Natural convection	Ψ_{jt}	3[6]	°C/W
	Maximum operating junction temperature	—	T_j	105	°C

Table 28. Oscillator and PLL Electrical Specifications (continued)

(V_{DD} and V_{DDPLL} = 2.7 to 3.6 V, V_{SS} = V_{SSPLL} = 0 V)

Characteristic	Symbol	Min	Max	Unit
Frequency un-LOCK range	f_{UL}	–1.5	1.5	% f_{ref}
Frequency LOCK range	f_{LCK}	–0.75	0.75	% f_{ref}
CLKOUT period jitter [4, 5, 10 ,11], measured at f_{SYS} Max • Peak-to-peak (clock edge to clock edge) • Long term (averaged over 2 ms interval)	C_{jitter}	 — —	 10 .01	% f_{sys}
On-chip oscillator frequency	f_{oco}	7.84	8.16	MHz

1 In external clock mode, it is possible to run the chip directly from an external clock source without enabling the PLL.

2 This value has been updated.

3 All internal registers retain data at 0 Hz.

4 Depending on packaging; see the orderable part number summary.

5 Loss of Reference Frequency is the reference frequency detected internally, which transitions the PLL into self clocked mode.

6 Self clocked mode frequency is the frequency at which the PLL operates when the reference frequency falls below f_{LOR} with default MFD/RFD settings.

7 This parameter is characterized before qualification rather than 100% tested.

8 Proper PC board layout procedures must be followed to achieve specifications.

9 This specification applies to the period required for the PLL to relock after changing the MFD frequency control bits in the synthesizer control register (SYNCR).

10 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{sys}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the PLL circuitry via V_{DDPLL} and V_{SSPLL} and variation in crystal oscillator frequency increase the C_{jitter} percentage for a given interval.

11 Based on slow system clock of 40 MHz measured at f_{sys} max.

2.9 USB Operation

Table 29. USB Operation Specifications

Characteristic	Symbol	Value	Unit
Minimum core speed for USB operation	$f_{sys\_USB\_min}$	16	MHz

2.10 General Purpose I/O Timing

GPIO can be configured for certain pins of the QSPI, DDR Control, timer, UART, Interrupt and USB interfaces. When in GPIO mode, the timing specification for these pins is given in Table 30 and Figure 5.

The GPIO timing is met under the following load test conditions:

- 50 pF / 50 Ω for high drive
- 25 pF / 25 Ω for low drive

Table 30. GPIO Timing

NUM	Characteristic	Symbol	Min	Max	Unit
G1	CLKOUT High to GPIO Output Valid	t_{CHPOV}	—	10	ns
G2	CLKOUT High to GPIO Output Invalid	t_{CHPOI}	1.5	—	ns
G3	GPIO Input Valid to CLKOUT High	t_{PVCH}	9	—	ns
G4	CLKOUT High to GPIO Input Invalid	t_{CHPI}	1.5	—	ns

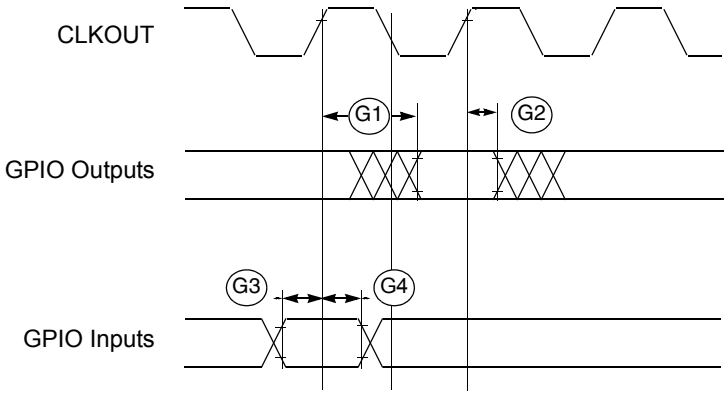


Figure 5. GPIO Timing

2.11 Reset Timing

Table 31. Reset and Configuration Override Timing

(V_{DD} = 3.0 to 3.6 V, V_{SS} = 0 V, $T_A = T_L$ to T_H)[1]

NUM	Characteristic	Symbol	Min	Max	Unit
R1	$\overline{\text{RSTI}}$ input valid to CLKOUT High	t_{RVCH}	9	—	ns
R2	CLKOUT High to $\overline{\text{RSTI}}$ Input invalid	t_{CHRI}	1.5	—	ns
R3	$\overline{\text{RSTI}}$ input valid time [2]	t_{RIVT}	5	—	t_{CYC}
R4	CLKOUT High to $\overline{\text{RSTO}}$ Valid	t_{CHROV}	—	10	ns

1 All AC timing is shown with respect to 50% V_{DD} levels unless otherwise noted.

2 During low power STOP, the synchronizers for the $\overline{\text{RSTI}}$ input are bypassed and $\overline{\text{RSTI}}$ is asserted asynchronously to the system. Thus, $\overline{\text{RSTI}}$ must be held a minimum of 100 ns.

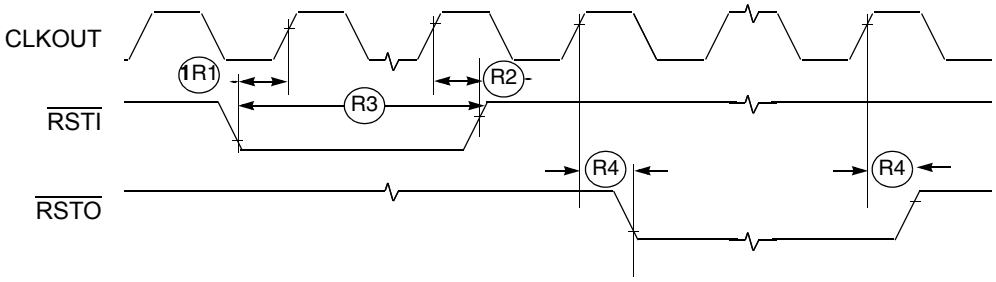


Figure 6. $\overline{\text{RSTI}}$ and Configuration Override Timing

2.12 I²C Input/Output Timing Specifications

Table 32 lists specifications for the I²C input timing parameters shown in Figure 7.

Table 32. I²C Input Timing Specifications between I2C_SCL and I2C_SDA

Num	Characteristic	Min	Max	Units
I1	Start condition hold time	$2 \times t_{CYC}$	—	ns
I2	Clock low period	$8 \times t_{CYC}$	—	ns
I3	SCL/SDA rise time (V_{IL} = 0.5 V to V_{IH} = 2.4 V)	—	1	ms
I4	Data hold time	0	—	ns
I5	SCL/SDA fall time (V_{IH} = 2.4 V to V_{IL} = 0.5 V)	—	1	ms
I6	Clock high time	$4 \times t_{CYC}$	—	ns
I7	Data setup time	0	—	ns
I8	Start condition setup time (for repeated start condition only)	$2 \times t_{CYC}$	—	ns
I9	Stop condition setup time	$2 \times t_{CYC}$	—	ns

Table 33 lists specifications for the I²C output timing parameters shown in Figure 7.

Table 33. I²C Output Timing Specifications between I2C_SCL and I2C_SDA

Num	Characteristic	Min	Max	Units
I1[1]	Start condition hold time	$6 \times t_{CYC}$	—	ns
I2[1]	Clock low period	$10 \times t_{CYC}$	—	ns
I3[2]	I2C_SCL/I2C_SDA rise time (V_{IL} = 0.5 V to V_{IH} = 2.4 V)	—	—	µs
I4[1]	Data hold time	$7 \times t_{CYC}$	—	ns
I5[3]	I2C_SCL/I2C_SDA fall time (V_{IH} = 2.4 V to V_{IL} = 0.5 V)	—	3	ns
I6[1]	Clock high time	$10 \times t_{CYC}$	—	ns
I7[1]	Data setup time	$2 \times t_{CYC}$	—	ns
I8[1]	Start condition setup time (for repeated start condition only)	$20 \times t_{CYC}$	—	ns
I9[1]	Stop condition setup time	$10 \times t_{CYC}$	—	ns

1 Output numbers depend on the value programmed into the IFDR; an IFDR programmed with the maximum frequency (IFDR = 0x20) results in minimum output timings as shown in Table 33. The I²C interface is designed to scale the actual data transition time to move it to the middle of the SCL low period. The actual position is affected by the prescale and division values programmed into the IFDR; however, the numbers given in Table 33 are minimum values.

2 Because SCL and SDA are open-collector-type outputs, which the processor can only actively drive low, the time SCL or SDA take to reach a high level depends on external signal capacitance and pull-up resistor values.

3 Specified at a nominal 50-pF load.

Figure 7 shows timing for the values in Table 32 and Table 33.

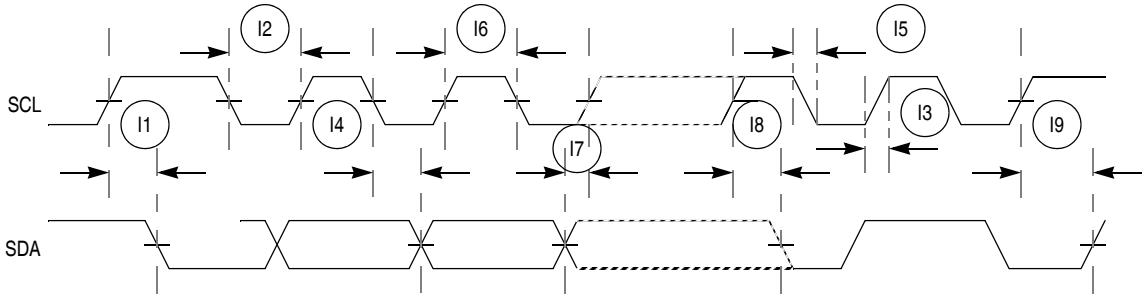


Figure 7. I²C Input/Output Timings

2.13 Analog-to-Digital Converter (ADC) Parameters

Table 34 lists specifications for the analog-to-digital converter.

Table 34. ADC Parameters[1]

Name	Characteristic	Min	Typical	Max	Unit
V_{REFL}	Low reference voltage	V_{SS}	—	V_{REFH}	V
V_{REFH}	High reference voltage	V_{REFL}	—	V_{DDA}	V
V_{DDA}	ADC analog supply voltage	3.0	3.3	3.6	V
V_{ADIN}	Input voltages	V_{REFL}	—	V_{REFH}	V
RES	Resolution	12	—	12	Bits
INL	Integral non-linearity (full input signal range)[2]	—	±2.5	±3	LSB[3]
INL	Integral non-linearity (10% to 90% input signal range)[4]	—	±2.5	±3	LSB
DNL	Differential non-linearity	—	–1 < DNL < +1	<+1	LSB
Monotonicity		GUARANTEED			
f_{ADIC}	ADC internal clock	0.1	—	5.0	MHz
R_{AD}	Conversion range	V_{REFL}	—	V_{REFH}	V
t_{ADPU}	ADC power-up time[5]	—	6	13	t_{AIC} cycles[6]
t_{REC}	Recovery from auto standby	—	0	1	t_{AIC} cycles
t_{ADC}	Conversion time	—	6	—	t_{AIC} cycles
t_{ADS}	Sample time	—	1	—	t_{AIC} cycles
C_{ADI}	Input capacitance	—	See Figure 8	—	pF
X_{IN}	Input impedance	—	See Figure 8	—	W
I_{ADI}	Input injection current[7], per pin	—	—	3	mA
I_{VREFH}	V_{REFH} current	—	0	—	mA
V_{OFFSET}	Offset voltage internal reference	—	±8	±15	mV
E_{GAIN}	Gain error (transfer path)	.99	1	1.01	—
V_{OFFSET}	Offset voltage external reference	—	±3	9	mV
SNR	Signal-to-noise ratio	—	62 to 66	—	dB

2.15 DMA Timers Timing Specifications

Table 35 lists timer module AC timings.

Table 35. Timer Module AC Timing Specifications

Name	Characteristic[1]	Min	Max	Unit
T1	DTIN0 / DTIN1 / DTIN2 / DTIN3 cycle time	$3 \times t_{CYC}$	—	ns
T2	DTIN0 / DTIN1 / DTIN2 / DTIN3 pulse width	$1 \times t_{CYC}$	—	ns

1 All timing references to CLKOUT are given to its rising edge.

2.16 QSPI Electrical Specifications

Table 36 lists QSPI timings.

Table 36. QSPI Modules AC Timing Specifications

Name	Characteristic	Min	Max	Unit
QS1	QSPI_CS[3:0] to QSPI_CLK	1	510	t_{CYC}
QS2	QSPI_CLK high to QSPI_DOUT valid	—	10	ns
QS3	QSPI_CLK high to QSPI_DOUT invalid (Output hold)	2	—	ns
QS4	QSPI_DIN to QSPI_CLK (Input setup)	9	—	ns
QS5	QSPI_DIN to QSPI_CLK (Input hold)	9	—	ns

The values in Table 36 correspond to Figure 9.

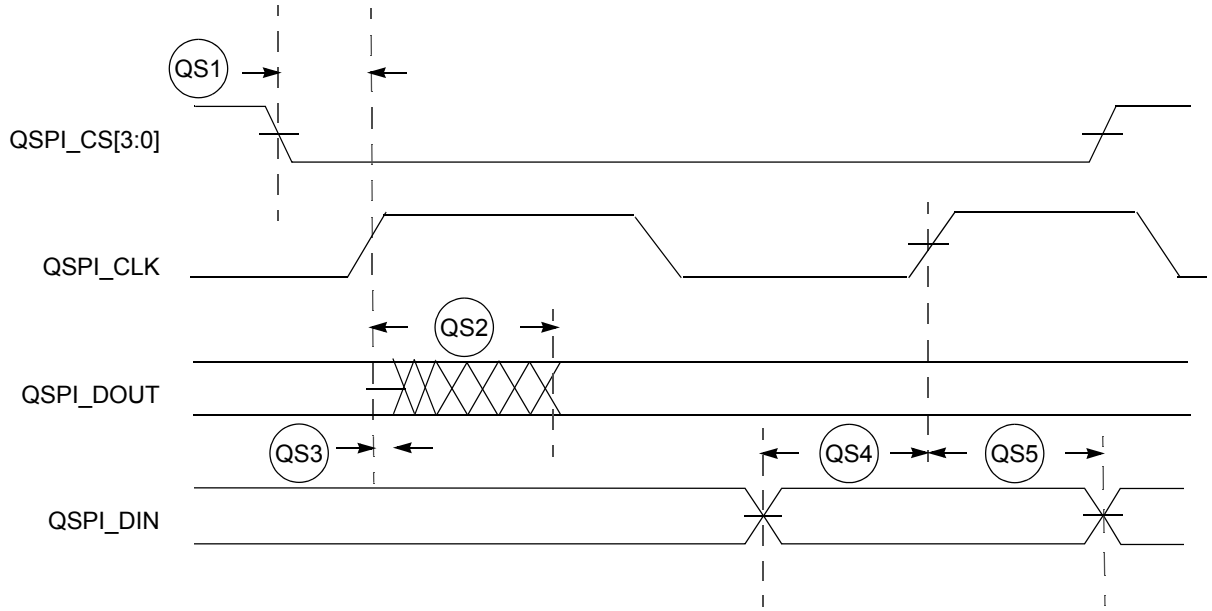


Figure 9. QSPI Timing

2.17 JTAG and Boundary Scan Timing

Table 37. JTAG and Boundary Scan Timing

Num	Characteristics[1]	Symbol	Min	Max	Unit
J1	TCLK frequency of operation	f_{JCYC}	DC	1/4	$f_{sys/2}$
J2	TCLK cycle period	t_{JCYC}	$4 \times t_{CYC}$	—	ns
J3	TCLK clock pulse width	t_{JCW}	26	—	ns
J4	TCLK rise and fall times	t_{JCRF}	0	3	ns
J5	Boundary scan input data setup time to TCLK rise	t_{BSDST}	4	—	ns
J6	Boundary scan input data hold time after TCLK rise	t_{BSDHT}	26	—	ns
J7	TCLK low to boundary scan output data valid	t_{BSDV}	0	33	ns
J8	TCLK low to boundary scan output high Z	t_{BSDZ}	0	33	ns
J9	TMS, TDI input data setup time to TCLK rise	t_{TAPBST}	4	—	ns
J10	TMS, TDI Input data hold time after TCLK rise	t_{TAPBHT}	10	—	ns
J11	TCLK low to TDO data valid	t_{TDODV}	0	26	ns
J12	TCLK low to TDO high Z	t_{TDODZ}	0	8	ns
J13	$\overline{\text{TRST}}$ assert time	t_{TRSTAT}	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	t_{TRSTST}	10	—	ns

1 JTAG_EN is expected to be a static signal. Hence, it is not associated with any timing.

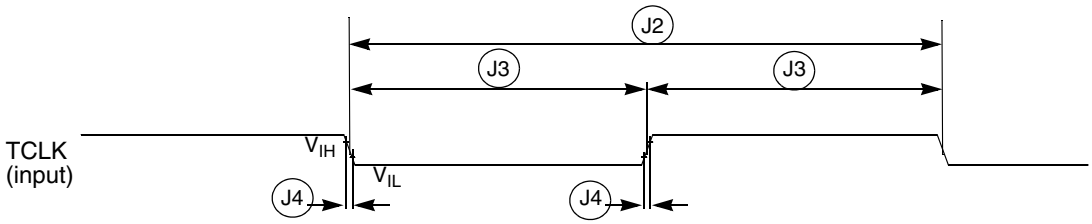
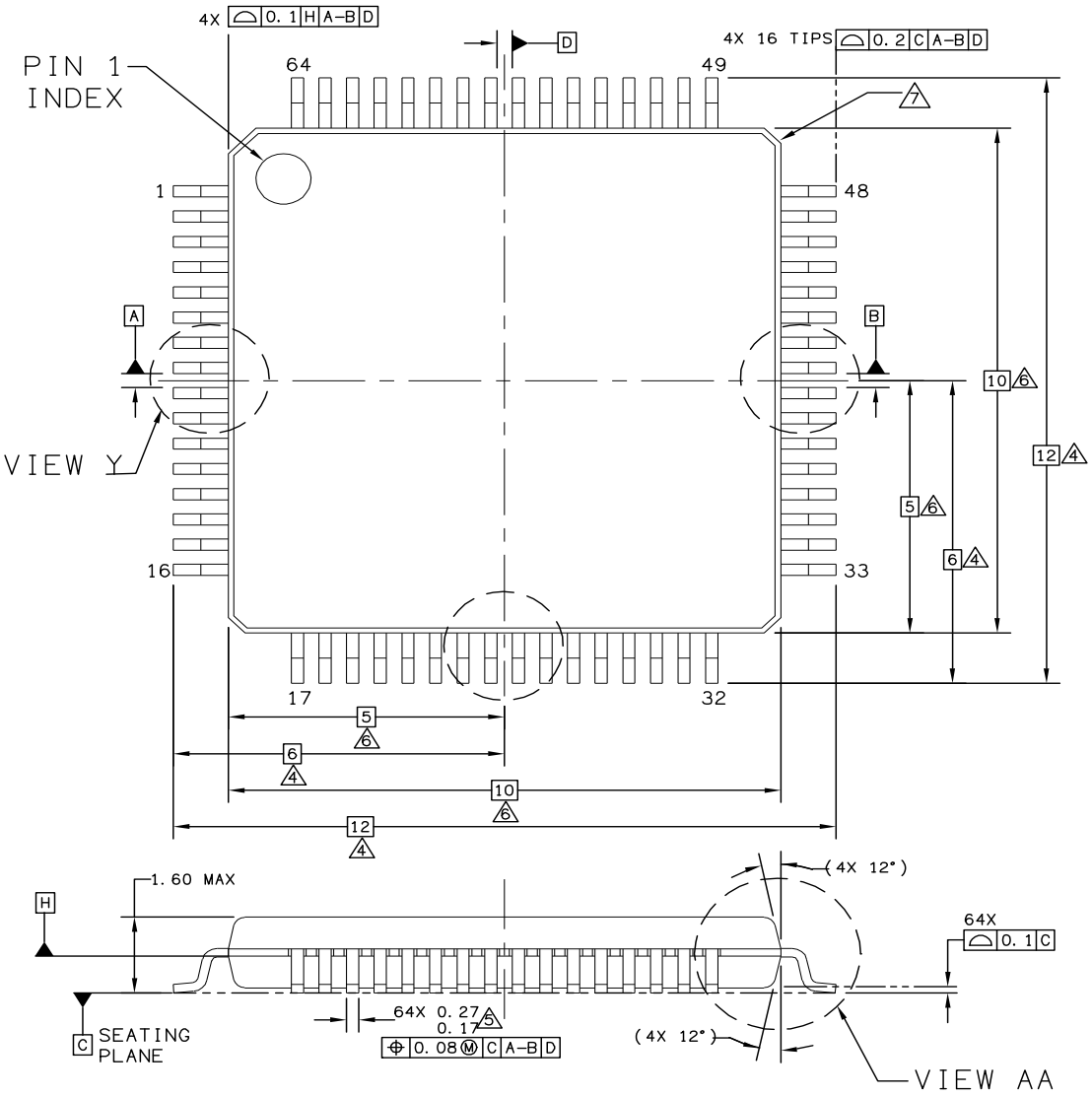


Figure 10. Test Clock Input Timing

3.1 64-pin LQFP Package



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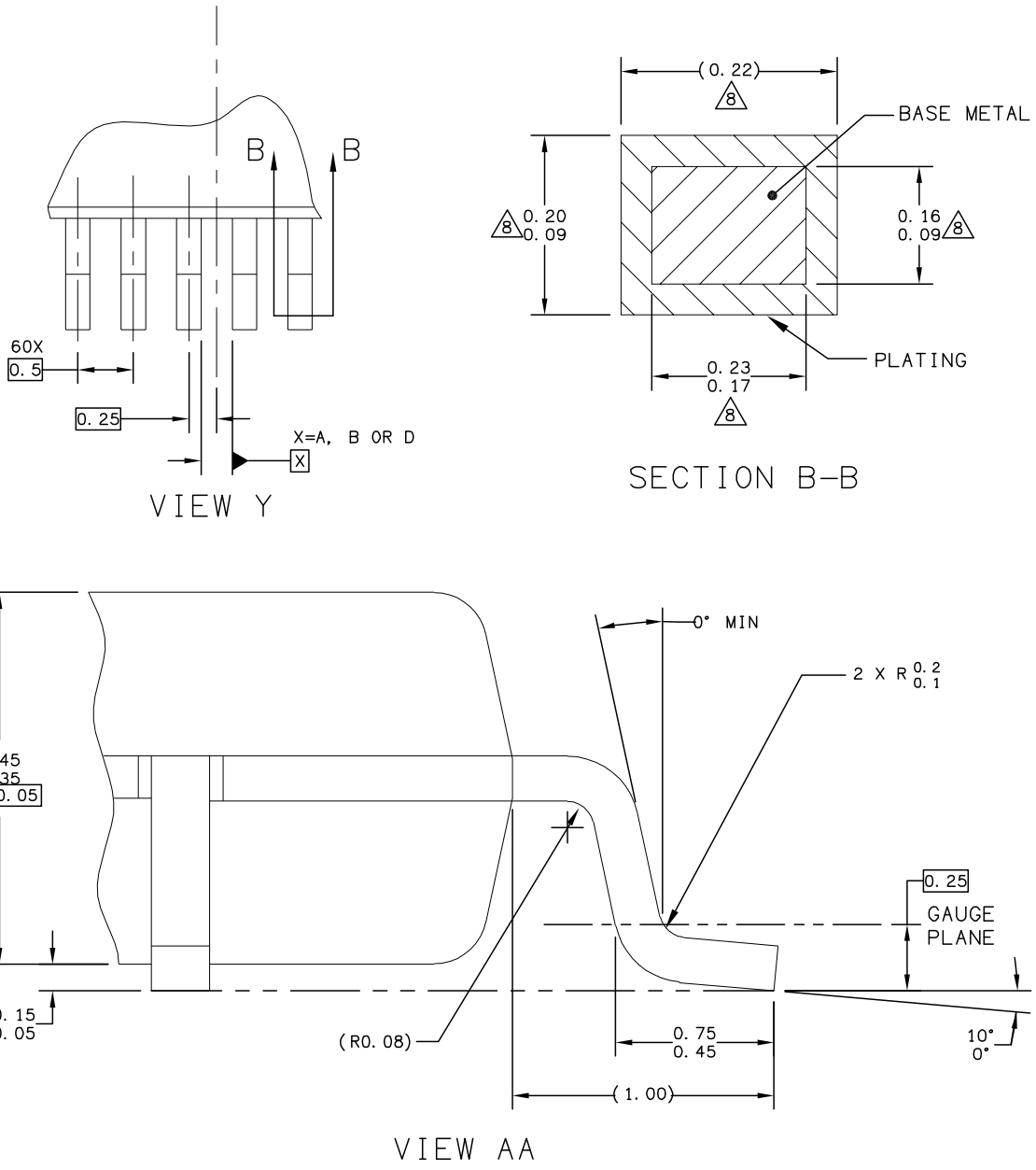
	CASE NUMBER: 840F-02	06 APR 2005
	STANDARD: JEDEC MS-026 BCD	



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NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.
3. THE COMPLETE JEDEC DESIGNATOR FOR THIS PACKAGE IS: HF–PQFN.
4. COPLANARITY APPLIES TO LEADS, CORNER LEADS AND DIE ATTACH PAD.
5. MIN METAL GAP SHOULD BE 0.2MM.

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	STANDARD: JEDEC MO–220 VMMD–3	
	PACKAGE CODE: 6200	SHEET: 3 OF 4

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